

No.710D ·

DS-1-35

Diffused Junction Type Silicon Diode

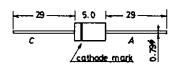
1.0A Power Rectifier

Features

- · Plastic molded type
- · Peak reverse voltage $V_{RM} = -100 \text{ to } -400 \text{V}$
- · Average rectified current Io=1.0A

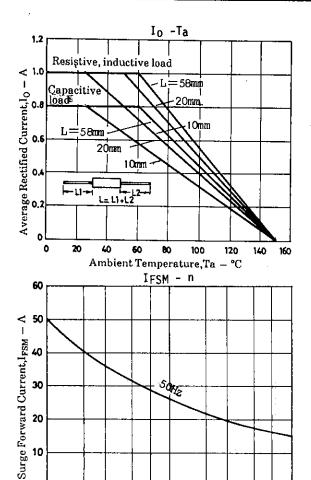
Absolute Maximum Ratings Peak Reverse Voltage Average Rectified Current Surge Forward Current Junction Temperature Storage Temperature	at Ta= V _{RM} I _O I _{FSM} Tj Tstg	25°C Ta=60°C 50Hz sine wave,1 cycle	DS135E -100 → → →	DS135D -200 → . → 40	DS135C unit -400 V 1.0 A 50 A 150 °C to +150 °C
Electrical Characteristics at Forward Voltage Reverse Current	$Ta = 25$ V_F I_R	S°C I _F =1.0A V _R : At each V _{RM}		min ty	rp max unit 1.0 V -10 μA

Package Dimensions 1005 (unit: mm)





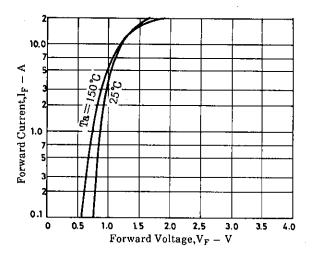
C: Cathode A: Anode



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Number of Cycles at 50Hz,n

20



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